PATENT APPLICATION

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UST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

MA) 10	G.G.P. van GORKOM et al., "Performance of Silicon Cold Cathodes", September 30, 1985, J. Vac. Sci. Technol. B 4(1), Jan/Feb 1986, pp. 108-111.
A IR	A.M.E. Hoeberechts et al., "Design, Technology, and Behavior of a Silicon Avalanche Cathode", October 8, 1985, J. Vac. Sci. Technol. B 4(1), Jan/Feb 1986, pp. 105-107.
15	E.A. Hijzen et al., "Avalanche Cold Cathodes with 10% Emission Efficiency", September 8-10, 1988, ESSDERC'98 Proceedings of the 28th European Solid-State Device Research Conference, pp. 584-587.

DATE CONSIDERED

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PATENT APPLICATION

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LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT

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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

M	10	Yokoo et al., "Experiments of highly emissive metal-oxide-semiconductor electron tunneling cathode", May/June 1996, J. Vac. Sci. Technol. B 14(3), 1996 American Vacuum Society, pp. 2096-2099.
JAP .	1R	Akinwande, A.I. et al., "GaN Solid State Electron Emitter", Technical Digest of IVMC'97, Kyongiu, Korea 1997, pp. 602-607.
	18	Lee, W.S. et al., "A Study on the Diamond Cold Cathode in FED", Asia Display 98, pp. 681-684.
EXAMIN		DATE CONSIDERED, 9/9/02

PATENT APPLICATION

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FORM PTO-1449	W.	ator
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APPLICATION NO. CONFIRMATION NO. 10007286-1 09/975,297 APPLICANT Ossipov t al. 10/12/01

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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

M	1Q	Komoda et al., "Mechanism of efficient and stable surface-emitting cold cathode based on porous polycrystalline silicon films", May/June 1999, J. Vac. Sci. Technol. B 17(3), 1999 American Vacuum Society, pp. 1076-1079.
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EXAMIN		Hamal Date considered 9/19/07